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SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

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KTA1273T

Complementary pair with KTA1273T.

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High current application.

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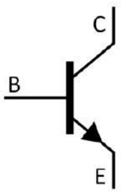

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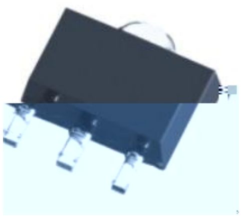

PIN1 Base PIN 2 Collector PIN 3 Emitter

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h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320
Marking	HP5O ⁑	HP5Y ⁑

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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Collector Emitter – Continuous	I_E	-2.0	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

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Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	30			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=1.0mA I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V I_E=0			0.1	A
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	A
DC Current Gain	h_{FE}	V_{CE}=2.0V I_C=500mA	100		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=1.5A I_B=0.03A			2.0	V
Base to Emitter Voltage	V_{BE}	V_{CE}=2.0V I_C=500mA			1.0	V
Transition Frequency	f_T	V_{CE}=2.0V I_C=500mA		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		13		pF

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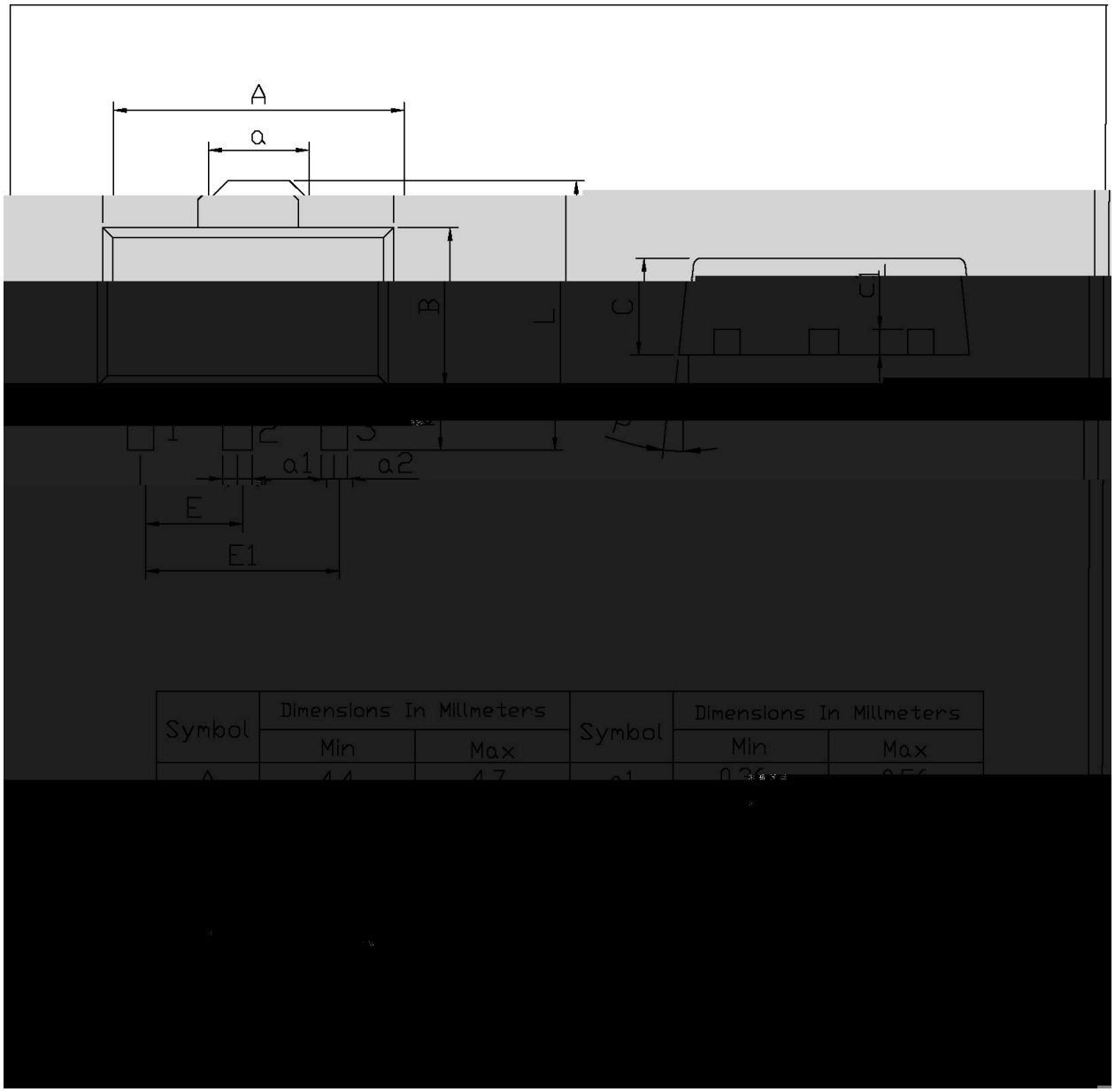
SOT-89

单位：mm



Symbol	Dimensions In Millmeters		Symbol	Dimensions In Millmeters	
	Min	Max		Min	Max
A	4.4	4.7	a1	0.36	0.56

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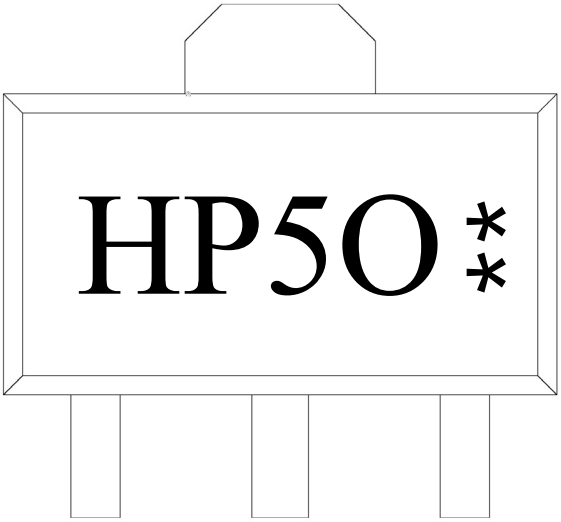

H

P5

O h_{FE}

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Note:

H: Company Code.

P5: Product Type.

O h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

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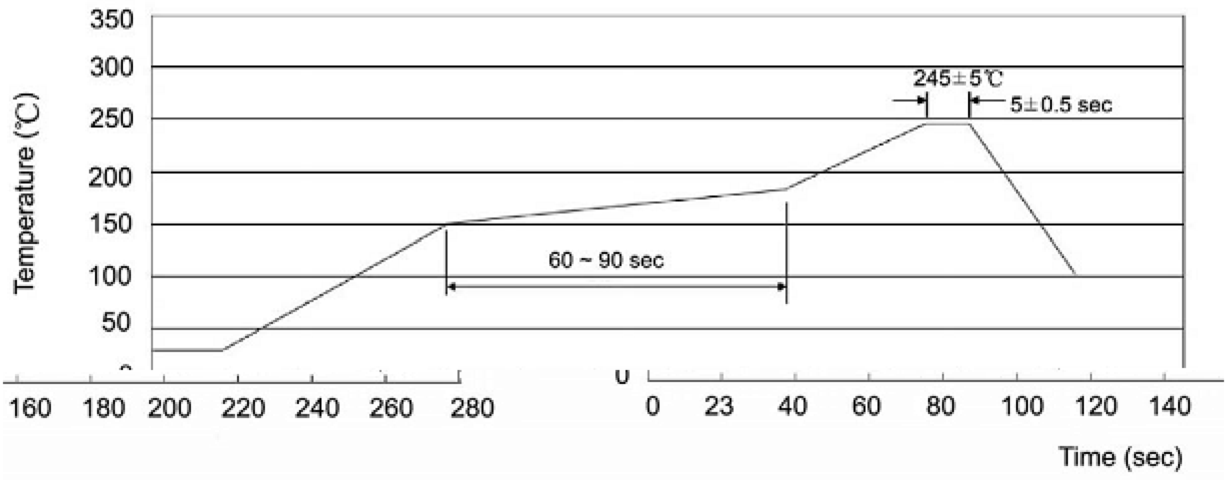

	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只卷盘	卷盘盒	只盒	盒箱	只箱		盒	箱